Hailan river

HCO65S20D1

*e*SiC Silicon Carbide Schottky Diode

650 V, 20 A

Features

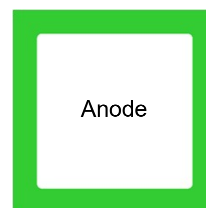
- No reverse recovery current
- Low forward voltage
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature

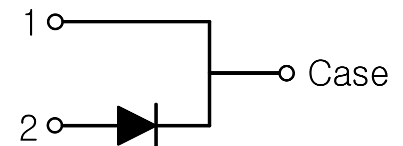
V_{RRM}	I_F	$T_{J,max}$	Q_C
650 V	20 A	175 ℃	77 nC

Applications

- Power Factor Correction
- Industrial Power Supplies
- Solar Inverter, UPS

Die Configuration





*Cathode : Bottom

Die Mechanical Parameters

Parameter	Typical Value	Unit
Wafer Diameter	6	inch
Die Dimensions (W x L x T)	2450 x 2450 x 180	μm
Anode Metallization (AlCu)	4	μm
Bottom Cathode Metallization (Ti/Ni/Ag)	0.5	μm
Recommended Source Bond Wire	Al 16mils x 2	ea
Gross Die (Single chip of wafer)	2,626	ea

Electrical Characteristics (T_J = 25℃) (Note1)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_F	Forward Voltage	I_F = 20 A, T_C = 25℃		1.30	1.60	V
I_R	Reverse Current	V_R = 650 V, T_C = 25℃		-	100	μA

1. Based on TO220 package.

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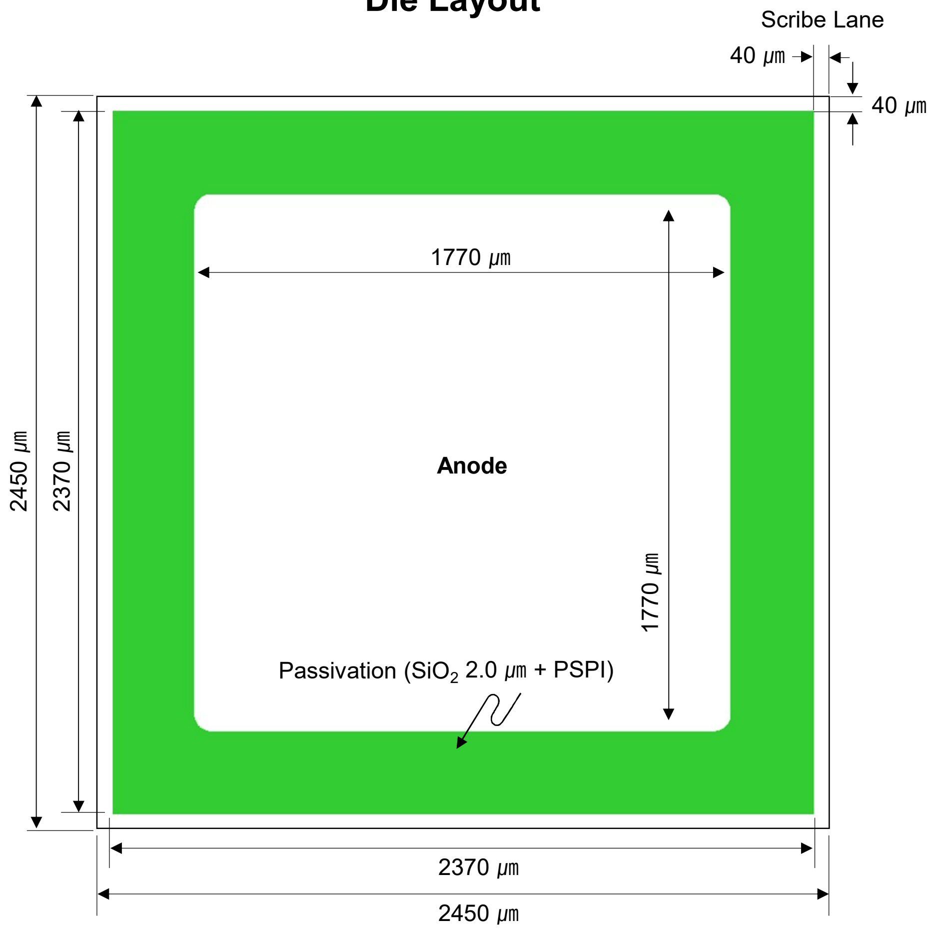
Die Layout



Wafer Sawing Information